

**Silicon NPN Power Transistors**

**2SC5358**

**DESCRIPTION**

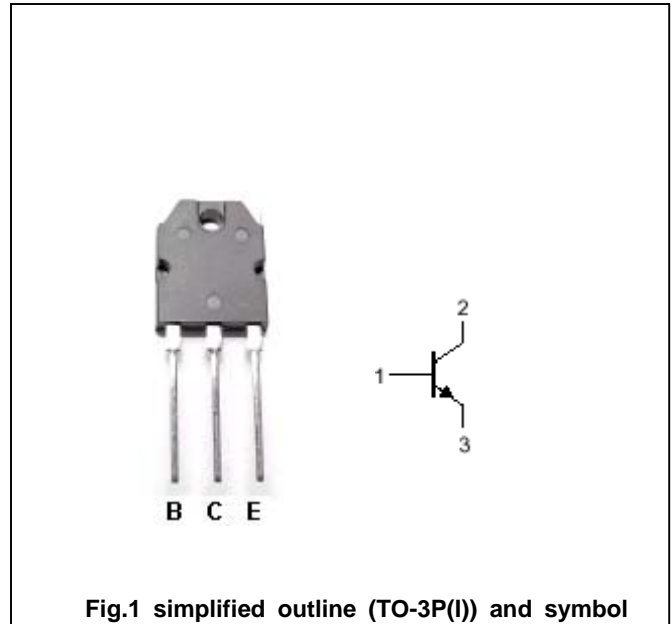
- With TO-3P(I) package
- Complement to type 2SA1986

**APPLICATIONS**

- Power amplifier applications
- Recommend for 80W high fidelity audio frequency amplifier output stage

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



**Absolute maximum ratings(Tc=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	230	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	230	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		15	A
I <sub>B</sub>	Base current		1.5	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25	150	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA; I <sub>B</sub> =0	230			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8 A; I <sub>B</sub> =0.8A			3.0	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =7A; V <sub>CE</sub> =5V			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =230V I <sub>E</sub> =0			5	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			5	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =5V	55		180	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =7A; V <sub>CE</sub> =5V	35			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1A; V <sub>CE</sub> =5V		30		MHz
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V; f=1MHz		200		pF

◆ h<sub>FE-1</sub> classifications

R	O
55-110	90-180

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PACKAGE OUTLINE

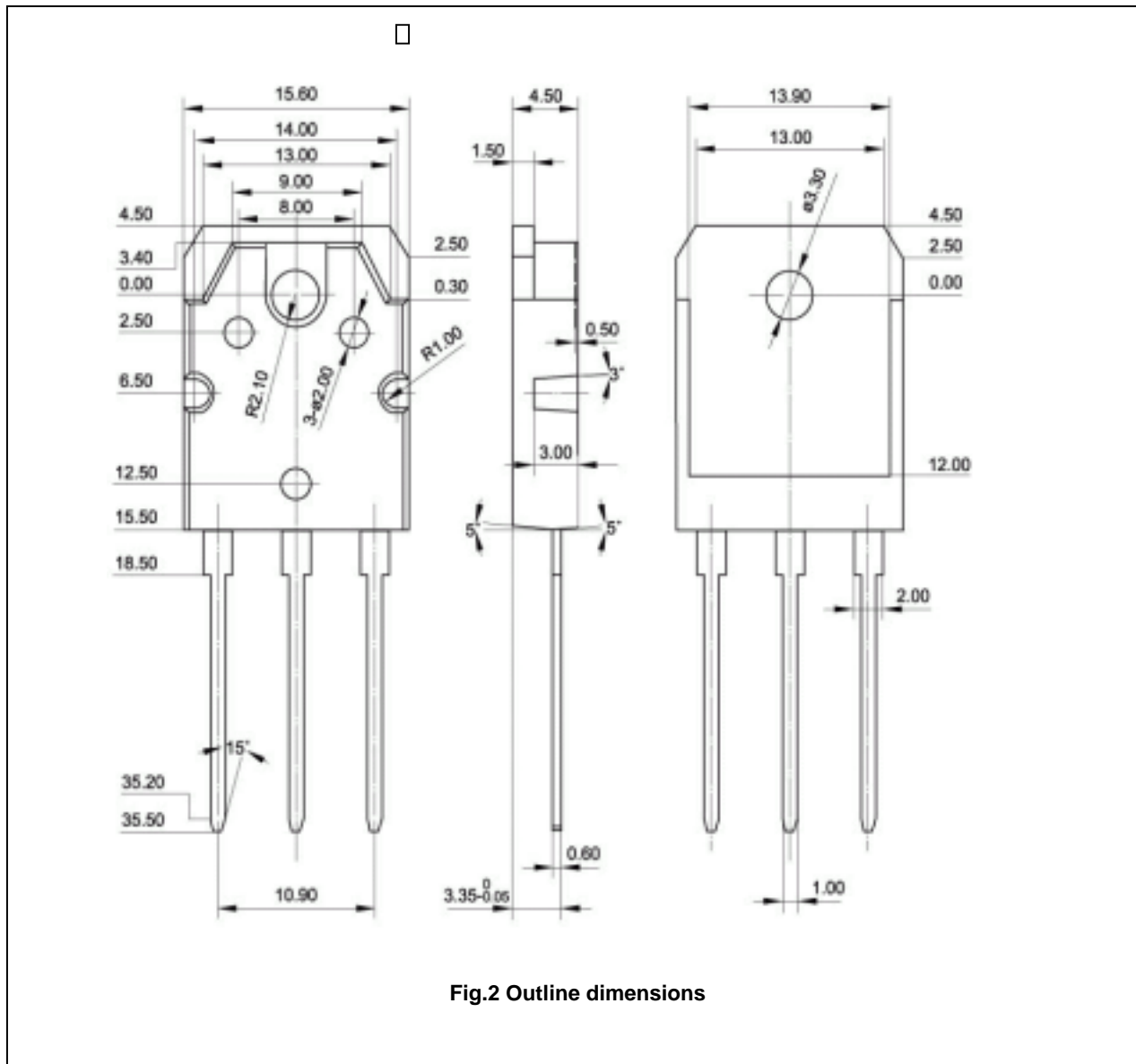


Fig.2 Outline dimensions